General Description

The MAX4634 fast, low-voltage, 4-channel CMOS analog multiplexer features 4Ω (max) on-resistance (R_{ON}). It offers R_{ON} matching between switches to 0.3Ω (max) and RON flatness of 1Ω (max) over the specified signal range. Each switch can handle V+ to GND analog signals. Off-leakage current is only 0.1nA (max) at +25°C. The MAX4634 features fast turn-on (ton) and turn-off (tOFF) times of 18ns and 11ns, respectively. All this comes in the tiny 10-pin µMAX® and 10-pin, 3mm x 3mm, TDFN packages.

This low-voltage multiplexer operates from a +1.8V to +5.5V single supply. All digital inputs have +0.8V and +2.4V logic thresholds, ensuring TTL/CMOS-logic compatibility with +5V operation.

Features

- Guaranteed Ron 2.5 Ω (typ) with 5V Supply 4.5 Ω (typ) with 3V Supply
- ♦ 0.3Ω (max) Guaranteed RON Match Between Channels
- 1Ω (max) Guaranteed Ron Flatness Over Signal Range
- 0.1nA (at +25°C) Guaranteed Low Leakage Currents
- ♦ +1.8V to +5.5V Single-Supply Operation
- +1.8V Operation $R_{ON} = 30\Omega$ (typ) Overtemperature $t_{ON} = 30$ ns (typ), $t_{OFF} = 13$ ns (typ)
- V+ to GND Signal Handling
- TTL/CMOS-Logic Compatible
- -78dB Crosstalk (at 1MHz)
- -80dB Off-Isolation (at 1MHz)
- 0.018% Total Harmonic Distortion

Ordering Information

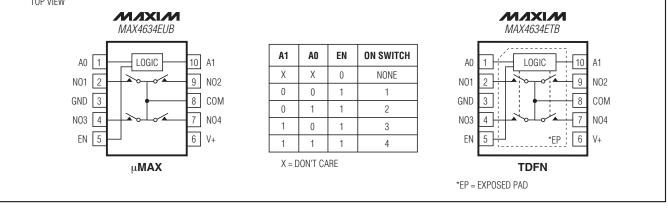
PART	TEMP RANGE	PIN-PACKAGE	TOP MARK
MAX4634EUB	-40°C to +85°C	10 µMAX	_
MAX4634ETB	-40°C to +85°C	10 TDFN-EP* (3mm x 3mm)	AAU

µMAX is a registered trademark of Maxim Integrated Products, Inc.

*EP = Exposed pad.

Pin Configurations/Functional Diagrams/Truth Table

TOP VIEW MAXIM MAXIM MAX4634EUB MAX4634ETB ON SWITCH A1 AO EN A0 1 LOGIC 10 A1 LOGIC A1 A0 10 Х Х 0 NONE N01 2 9 NO2 N01 9 N02 0 0 1 1 8 COM GND 3 GND COM 3 8 2 0 1 1



Maxim Integrated Products 1

MAX4634

For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

Applications

Battery-Operated Equipment Audio and Video Signal Routing Low-Voltage Data-Acquisition Systems Sample-and-Hold Circuits **Communications Circuits**

ABSOLUTE MAXIMUM RATINGS

(Voltages referenced to GND.)

V+	0.3V to +6V
A_, EN, COM, NO_ (Note 1)	0.3V to (V+ + 0.3V)
Continuous Current (all other pins)	±20mA
Continuous Current (COM, NO_)	±50mA
Peak Current (COM, NO_ pulsed at 1ms,	
10% duty cycle)	±100mA

Continuous Power Dissipation ($T_A = +70^\circ$	°C)
10-Pin µMAX (derate 4.1mW/°C above	+70°C)330mW
10-Pin TDFN (derate 24.4mW/°C	
above +70°C)	1951mW
Operating Temperature Range	40°C to +85°C
Storage Temperature Range	
Lead Temperature (soldering, 10s)	+300°C

Note 1: Signals on NO_, COM, EN, or A_ exceeding V+ or GND are clamped by internal diodes. Limit forward diode current to maximum current rating.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS—Single +5V Supply

(V+ = +4.5V to +5.5V, V_{IH} = 2.4V, V_{IL} = 0.8V, T_A = -40°C to +85°C, unless otherwise noted. Typical values are at V+ = +5V, T_A = +25°C.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS	
ANALOG SWITCH				-				
Analog Signal Range	V _{COM} , V _{NO} _			0		V+	V	
On-Resistance	Devi	$V_{+} = 4.5V,$	$T_A = +25^{\circ}C$		2.5	4	Ω	
On-Resistance	Ron	$I_{COM} = 10mA,$ $V_{NO} = 0 \text{ to V}+$	$T_A = T_{MIN}$ to T_{MAX}			4.5	52	
On-Resistance Match		$V_{+} = 4.5V,$	$T_A = +25^{\circ}C$		0.1	0.3		
Between Channels (Notes 4, 5)	ΔRon	$I_{COM} = 10mA,$ $V_{NO} = 0 \text{ to V}+$	$T_A = T_{MIN}$ to T_{MAX}			0.4	Ω	
On-Resistance Flatness	RFLAT(ON) ICOM = 10mA,	T _A = +25°C		0.75	1			
(Note 6)			TA = TMIN to TMAX			1.2	Ω	
NO_ Off-Leakage		V + = 5.5V;	$T_A = +25^{\circ}C$	-0.1	±0.01	+0.1	nA	
Current (Note 7)	INO_(OFF)	$V_{COM} = 1V, 4.5V;$ $V_{NO} = 4.5V, 1V$	$T_A = T_{MIN}$ to T_{MAX}	-0.3		+0.3		
COM Off-Leakage Current		$V_{+} = 5.5V;$	$T_A = +25^{\circ}C$	-0.1	±0.01	+0.1		
(Note 7)	ICOM(OFF)	$V_{COM} = 1V, 4.5V;$ $V_{NO} = 4.5V, 1V$	$T_A = T_{MIN}$ to T_{MAX}	-0.65		+0.65	+0.65 nA	
COM On-Leakage Current	Leakage Current ICOM(ON)	$V_{+} = 5.5V;$ $V_{COM} = 1V, 4.5V;$ $T_{A} = +25^{\circ}C$		-0.1	±0.01	+0.1	nA	
(Note 7)		$V_{NO} = 1V, 4.5V,$ or unconnected	$T_A = T_{MIN}$ to T_{MAX}	-0.65		+0.65		
DIGITAL I/O (A_, EN)							1	
Input Logic-High	VIH			2.4			V	
Input Logic-Low	VIL					0.8	V	
Input Logic Current				-100	5	+100	nA	

ELECTRICAL CHARACTERISTICS—Single +5V Supply (continued)

(V+ = +4.5V to +5.5V, V_{IH} = 2.4V, V_{IL} = 0.8V, T_A = -40°C to +85°C, unless otherwise noted. Typical values are at V+ = +5V, T_A = +25°C.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
DYNAMIC		I		1			1
Turn-On Time (Note 7)	ton	$V_{NO_{-}} = 3V,$ $R_{L} = 300\Omega,$	$T_A = +25^{\circ}C$		14	18	ns
	UN	$C_L = 35 pF$, Figure 2	TA = TMIN to TMAX			20	
Turn-Off Time (Note 7)	lote 7) t _{OFF}	$V_{NO_{-}} = 3V,$ $R_{I_{-}} = 300\Omega,$	$T_A = +25^{\circ}C$		6	11	ns
	UFF	$C_L = 35pF$, Figure 2	$T_A = T_{MIN}$ to T_{MAX}			13	115
Break-Before-Make Time	topu	$V_{NO_{-}} = 3V,$ $R_{I_{-}} = 300\Omega,$	$T_A = +25^{\circ}C$		8		
(Note 7)	^t BBM	$C_{L} = 35 \text{pF}$, Figure 3	$T_A = T_{MIN}$ to T_{MAX}	1			– ns
Charge Injection	Q	$V_{\text{GEN}} = 2V, R_{\text{GEN}} = 0,$	$V_{GEN} = 2V, R_{GEN} = 0, C_L = 5pF, Figure 4$		2		рС
Off-Isolation (Note 8)	Viso	$C_L = 5 pF, R_L = 50 \Omega,$	f = 10MHz		-57		- dB
	V150	Figure 5	f = 1MHz		-80		
Crosstalk (Note 9)	Vot	$C_L = 5 pF, R_L = 50 \Omega,$	f = 10MHz		-52		- dB
CIOSSIAIR (NOLE 9)	VCT	Figure 5	f = 1MHz		-78		
NO_Off-Capacitance	C _{NO_(OFF)}	Figure 6			13		pF
COM Off-Capacitance	CCOM(OFF)	Figure 6			52		pF
COM On-Capacitance	CCOM(ON)	C _L = 5pF, Figure 6			68		pF
Total Harmonic Distortion	THD	$R_L = 600\Omega$, f = 20Hz to 20kHz			0.018		%
POWER SUPPLY		1		1			
Power-Supply Range	V+			1.8		5.5	V
Positive Supply Current	+	V+ = 5.5V, V _{IH} = V+, V	/ _{IL} = 0		0.001	1.0	μA

ELECTRICAL CHARACTERISTICS—Single +3V Supply

 $(V + = +2.7V \text{ to } +3.3V, V_{IH} = 2.0V, V_{IL} = 0.4V, T_A = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V + = +3V, T_A = +25^{\circ}\text{C}.)$ (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
ANALOG SWITCH		·					
Analog Signal Range	Vcom, V _{NO} _			0		V+	V
On-Resistance	Pou	$V_{+} = 2.7V,$ ICOM = 10mA,	$T_A = +25^{\circ}C$		4.5	7	Ω
On-nesistance	Ron	$V_{NO} = 0$ to V+				8	52
On-Resistance Match Between Channels	ΔRon	V+ = 2.7V, I _{COM} = 10mA,	$T_A = +25^{\circ}C$		0.1	0.3	Ω
(Notes 4, 5)		$V_{NO} = 0$ to V+	$T_A = T_{MIN}$ to T_{MAX}			0.4	

ELECTRICAL CHARACTERISTICS—Single +3V Supply (continued)

 $(V + = +2.7V \text{ to } +3.3V, V_{IH} = 2.0V, V_{IL} = 0.4V, T_A = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V + = +3V, T_A = +25^{\circ}\text{C}.)$ (Notes 2, 3)

PARAMETER	SYMBOL	COND	ITIONS	MIN	ТҮР	MAX	UNITS	
On-Resistance Flatness		$V_{+} = 2.7V,$	$T_A = +25^{\circ}C$		1.2	2.5	0	
(Note 6)	RFLAT(ON)	$I_{COM} = 10mA,$ $V_{NO} = 0 \text{ to V}+$	TA = TMIN to TMAX			3	Ω	
NO_ Off-Leakage Current		_(OFF) V+ = 3.3V; VCOM = 1V, 3V; VNO_= 3V, 1V	$T_A = +25^{\circ}C$	-0.1	±0.01	+0.1		
(Note 7)	I _{NO_(OFF)}		$T_A = T_{MIN}$ to T_{MAX}	-0.3		+0.3	nA	
COM Off-Leakage Current		$V_{+} = 3.3V;$ $V_{COM} = 1V, 3V;$	$T_A = +25^{\circ}C$	-0.1	±0.01	+0.1	nA	
(Note 7)	ICOM(OFF)	$V_{\rm NO} = 10, 30, V_{\rm NO} = 3V, 1V$	$T_A = T_{MIN}$ to T_{MAX}	-0.65		+0.65		
COM On-Leakage Current		V+ = 3.3V; V _{COM} = 1V, 3V;	$T_A = +25^{\circ}C$	-0.1	±0.01	+0.1		
(Note 7)	ICOM(ON)	V_{NO} = 1V, 3V, or unconnected	$T_A = T_{MIN}$ to T_{MAX}	-0.65		+0.65	nA	
DIGITAL I/O (A_, EN)		1						
Input High	Vih			2.0			V	
Input Low	VIL					0.4	V	
Input Logic Current				-100	5	+100	nA	
DYNAMIC							-	
Turn-On Time (Note 7)	ton	$\begin{array}{l} V_{NO_}=2V,\\ C_L=35 pF,\\ R_L=300 \Omega, \mbox{ Figure 2} \end{array}$	$T_A = +25^{\circ}C$		16	22	ns	
			$T_A = T_{MIN}$ to T_{MAX}			24	- 115	
Turn-Off Time (Note 7)	toff	V _{NO} = 2V, C _L = 35pF,	$T_A = +25^{\circ}C$		8	14	ns	
	UFF	$R_L = 300\Omega$, Figure 2	$T_A = T_{MIN}$ to T_{MAX}			16	113	
Break-Before-Make Time	tBBM	V _{NO} _ = 2V, CL = 35pF,	$T_A = +25^{\circ}C$		9		ns	
(Note 7)	'GRINI	$R_L = 300\Omega$, Figure 3	TA = TMIN to TMAX	1			115	
Charge Injection	Q	$V_{GEN} = 1.5V, R_{GEN} =$	0, $C_L = 5 pF$, Figure 4		2		рС	
Off-Isolation (Note 8)	VISO	$C_L = 5 pF, R_L = 50 \Omega,$	f = 10MHz		-57		dB	
	• 150	Figure 5	f = 1MHz		-80			
Crosstalk (Note 9)	VCT	$C_L = 5pF, R_L = 50\Omega,$	f = 10MHz		-52		dB	
	VCI	Figure 5	f = 1MHz		-78			

ELECTRICAL CHARACTERISTICS—Single +3V Supply (continued)

(V+ = +2.7V to +3.3V, V_{IH} = 2.0V, V_{IL} = 0.4V, T_A = -40°C to +85°C, unless otherwise noted. Typical values are at V+ = +3V, T_A = +25°C.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS		TYP	MAX	UNITS
NO_ Off-Capacitance	CNO_(OFF)	V _{NO} = GND, f = 1MHz, Figure 6		13		pF
COM Off-Capacitance	CCOM(OFF)	V _{COM} = GND, f = 1MHz, Figure 6		52		pF
COM On-Capacitance	C _(ON)	$V_{COM} = V_{NO} = GND$, f = 1MHz, Figure 6		68		pF
Total Harmonic Distortion	THD	$R_L = 600\Omega$, f = 20Hz to 20kHz		0.018		%
POWER SUPPLY	I.					
Positive Supply Current	+	$V_{+} = 3.3V, V_{IH} = V_{+}, V_{IL} = 0$		0.001	1	μA

Note 2: The algebraic convention, where the most negative value is a minimum and the most positive value a maximum, is used in this data sheet.

Note 3: TDFN parts are tested at +25°C and guaranteed by design and correlation over the entire temperature range.

Note 4: $\Delta R_{ON} = R_{ON(MAX)} - R_{ON(MIN)}$.

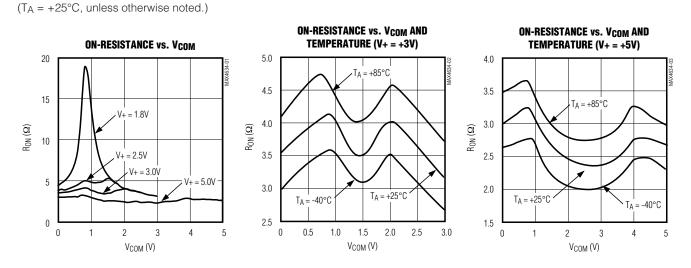
Note 5: R_{ON} and ΔR_{ON} matching specifications for TDFN-packaged parts are guaranteed by design.

Note 6: Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.

Note 7: Guaranteed by design.

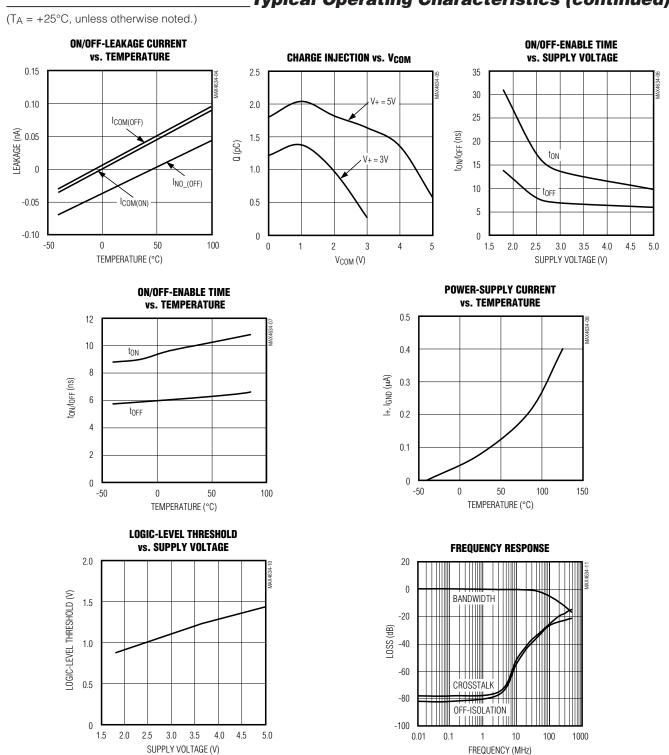
Note 8: Off-isolation = $20\log_{10} (V_{COM} / V_{NO})$, where V_{COM} = output and V_{NO} = input to off switch.

Note 9: Between any two switches.



Typical Operating Characteristics

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Typical Operating Characteristics (continued)

M NXI M

MAX4634

$\label{eq:Fast, Low-Voltage, 4} \Omega, \\ \mbox{4-Channel CMOS Analog Multiplexer}$

PIN			
μΜΑΧ/ TDFN	NAME	FUNCTION	
1	AO	Address Input. See the <i>Truth Table</i> for details.	
2	NO1	Normally Open Switch 1	
3	GND	Ground	
4	NO3	Normally Open Switch 3	
5	EN	Enable Logic Input. See the <i>Truth Table</i> for details.	
6	V+	Positive Supply Voltage. Connect to an external power supply. Bypass to GND with a 10µF capacitor placed as close to the pin as possible.	
7	NO4	Normally Open Switch 4	
8	COM	Analog Switch Common Terminal	
9	NO2	Normally Open Switch 2	
10	A1	Address Input. See the <i>Truth Table</i> for details.	
	EP	Exposed Pad. Internally connected to GND. Connect to a large PCB ground plane for proper operation. Not intended as an electrical connection point (TDFN package only).	

Pin Description

Detailed Description

The MAX4634 is a low-on-resistance, low-voltage analog multiplexer that operates from a +1.8V to +5.5V single supply. CMOS switch construction allows processing of analog signals that are within the supply voltage range (GND to V+).

To disable all switch channels, drive EN low. All four inputs and COM become high impedance during this state. If the disable feature is not needed, connect EN to V+.

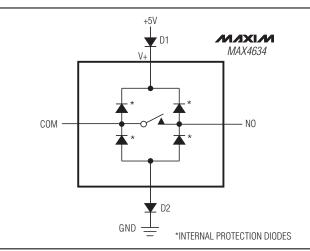


Figure 1. Overvoltage Protection Using External Blocking Diodes

Applications Information

Power-Supply Sequencing and Overvoltage Protection

Proper power-supply sequencing is recommended for all CMOS devices. Always apply V+ before applying analog signals or logic inputs, especially if the analog or logic signals are not current limited. If this sequencing is not possible, and if the analog or logic inputs are not current limited to < 20mA, add a small-signal diode (D1) as shown in Figure 1. If the analog signal can dip below GND, add D2. Adding protection diodes reduces the analog signal range to a diode drop (about 0.7V) below V+ for D1 or to a diode drop above ground for D2. The addition of diodes does not affect leakage. On-resistance increases by a small amount at low supply voltages. Maximum supply voltage (V+) must not exceed 6V.

Protection diodes D1 and D2 also protect against some overvoltage situations. A fault voltage up to the absolute maximum rating at an analog signal input does not damage the device, even if the supply voltage is below the signal voltage. **MAX463**4

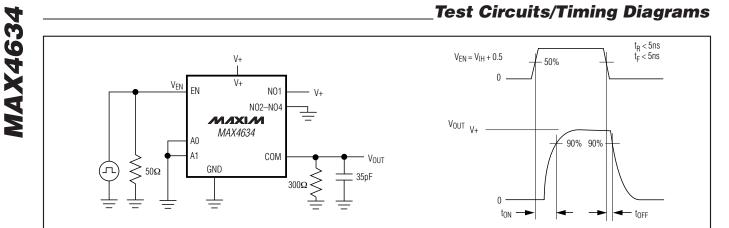


Figure 2. Switching Time

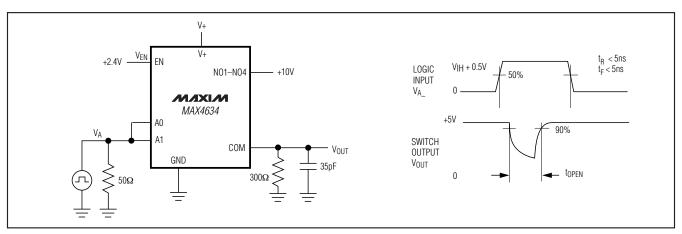


Figure 3. Break-Before-Make Interval

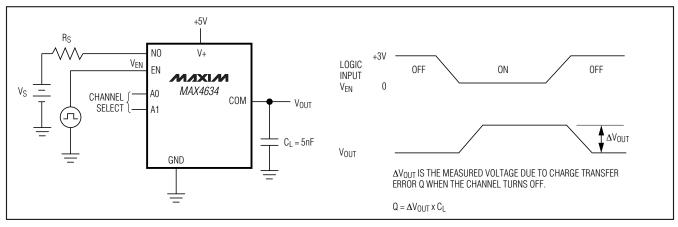


Figure 4. Charge Injection

Test Circuits/Timing Diagrams (continued)

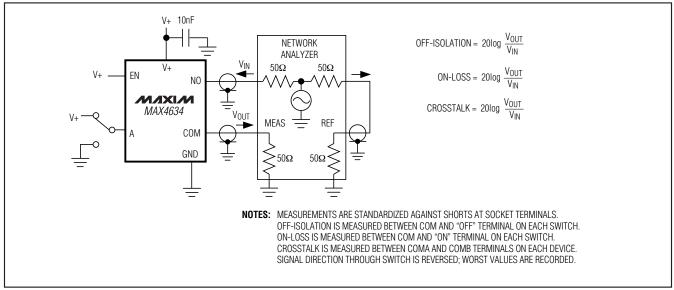


Figure 5. Off-Isolation/On-Channel Bandwidth

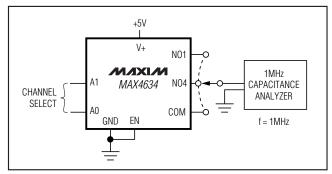


Figure 6. Channel Off/On-Capacitance

Chip Information

PROCESS: CMOS

Package Information

For the latest package outline information and land patterns, go to **www.maxim-ic.com/packages**.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
10 µMAX	—	<u>21-0061</u>
10 TDFN	T1033-1	<u>21-0137</u>

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	4/00	Initial release	—
1	2/02	Added QFN package	—
2	5/03	Added QFN packaging information	—
3	2/09	Added TDFN package information (replaced QFN), style edits	1, 7

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MAX4634

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